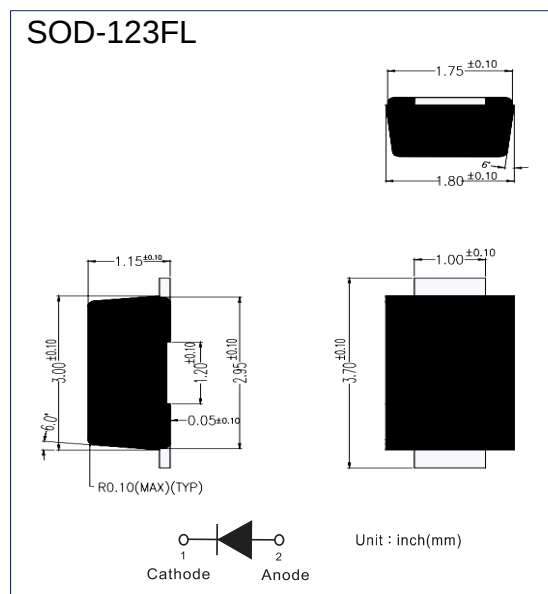


Features

- Low profile package
- Ideal for automated placement
- Guardring for overvoltage protection
- Low power losses, high efficiency
- High forward surge capability
- Compliant with RoHS standards, halogen-free

Mechanical Data

- Package: SOD-123FL
- Terminals: Tin plated leads, solderable per
- Polarity: Cathode line denotes the cathode end



Maximum Ratings (T_a=25℃ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	DSK32	DSK33	DSK34	DSK35	DSK36	DSK38	DSK310	DSK315	DSK320
Repetitive peak reverse voltage	VRRM	V	20	30	40	50	60	80	100	150	200
Average rectified output current @60Hz sine wave, Resistance load, Ta (FIG.1)	IO	A	3.0								
Surge(non-repetitive)forward current @60Hz half-sine wave,1 cycle, Tj=25℃	IFSM	A	65								
Storage temperature	Tstg	℃	-55 ~+150								
Junction temperature	Tj	℃	-55 ~+150						-55 ~+175		
Typical Junction Capacitance measured at 1MHz and Applied on 4.0VD.C	Cj	pF	165								



Electrical Characteristics

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	DSK32	DSK33	DSK34	DSK35	DSK36	DSK38	DSK310	DSK315	DSK320
Maximum instantaneous forward voltage drop per diode	V _F	V	I _{FM} =3.0A	0.55			0.70		0.85		0.95	
Maximum DC reverse current at rated DC blocking voltage per diode @ V _{RM} =V _{RRM}	I _{RRM}	mA	T _a =25°C	0.5					0.1			
			T _a =100°C	10					5			

Characteristics Curves

FIG1: I_o-T_L Curve

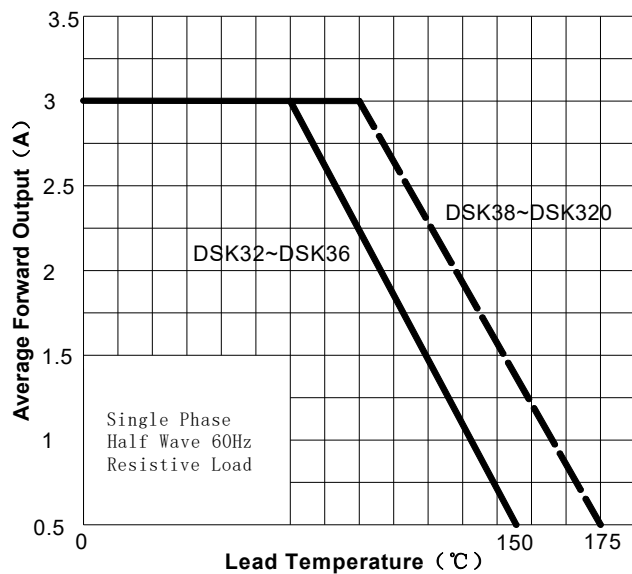


FIG2: Surge Forward Current Capability

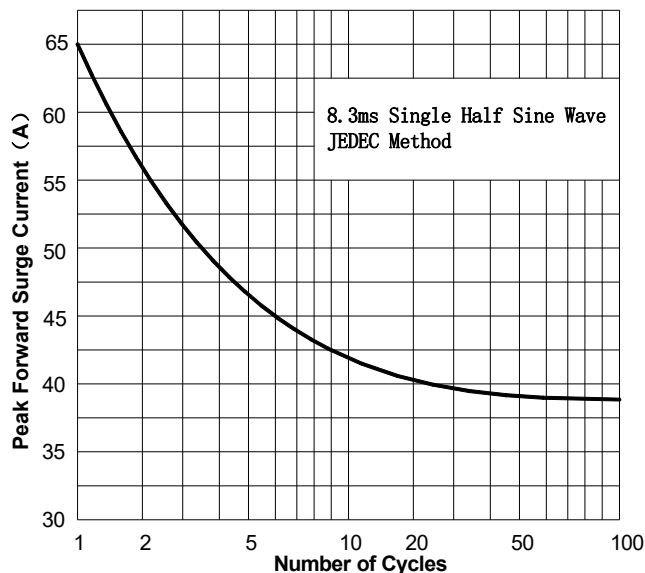


FIG3: Forward Voltage

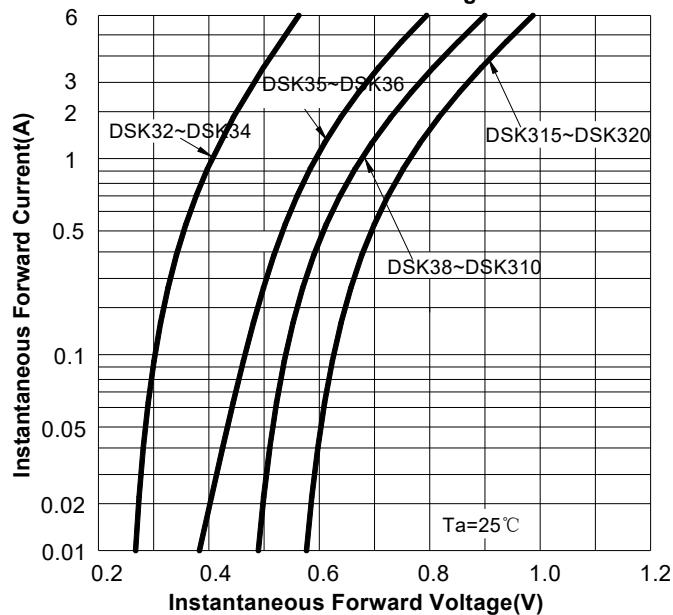


FIG4: Typical Reverse Characteristics

